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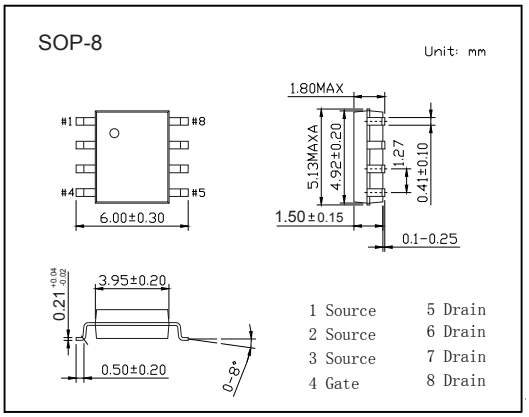
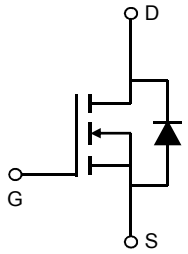


■ Features

- V_{DS} (V) = 40V
- I_D = 24 A (V_{GS} = 10V)
- $R_{DS(ON)}$ < 3.3mΩ (V_{GS} = 10V)
- $R_{DS(ON)}$ < 4.3mΩ (V_{GS} = 4.5V)



■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	TA=25℃	I_D	24	A
	TA=70℃		19	
Pulsed Drain Current		I_{DM}	170	
Avalanche Current		I_{AS}	75	
Avalanche energy	L=0.1mH	E_{AS}	281	mJ
Power Dissipation	TA=25℃	P_D	3.1	W
	TA=70℃		2	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R_{thJA}	40	℃/W
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R_{thJL}	24	
Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=250 uA, V_{GS}=0V	40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V, V_{GS}=0V			1	uA
		V_{DS}=40V, V_{GS}=0V, T_J=55℃			5	
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} , I_D=250uA	1.2		2.3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A			3.3	mΩ
		V_{GS}=10V, I_D=20A T_J=125℃			4.9	
		V_{GS}=4.5V, I_D=20A			4.3	
On State Drain Current	$I_{D(ON)}$	V_{GS}=10V, V_{DS}=5V	170			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=20A		90		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=20V, f=1MHz		4245		pF
Output Capacitance	C_{oss}			1170		
Reverse Transfer Capacitance	C_{rss}			69		
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.5		1.5	Ω
Total Gate Charge (10V)	Q_g	V_{GS}=10V, V_{DS}=20V, I_D=20A		62	87	nC
Total Gate Charge (4.5V)				28	40	
Gate Source Charge	Q_{gs}			10.5		
Gate Drain Charge	Q_{gd}			8		
Turn-On DelayTime	$t_{d(on)}$	V_{GS}=10V, V_{DS}=20V, R_L=1Ω, R_{GEN}=3Ω		9		ns
Turn-On Rise Time	t_r			11.5		
Turn-Off DelayTime	$t_{d(off)}$			42		
Turn-Off Fall Time	t_f			21		
Body Diode Reverse Recovery Time	t_{rr}	I_F= 20A, dI/dt= 500A/us		23		
Body Diode Reverse Recovery Charge	Q_{rr}			74		nC
Maximum Body-Diode Continuous Current	I_S				4.5	A
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4240 KC****

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■ Typical Characterisitics

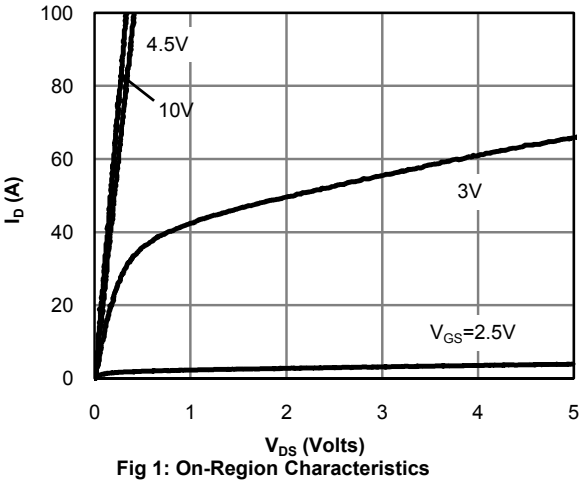

Fig 1: On-Region Characteristics

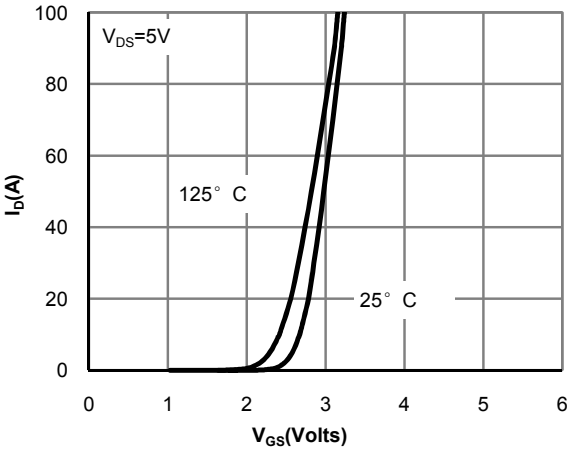

Figure 2: Transfer Characteristics

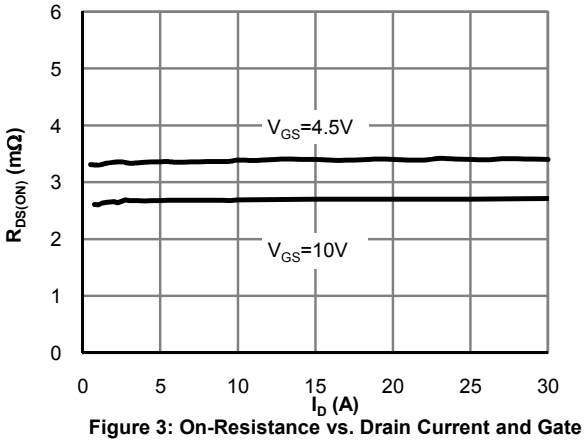

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

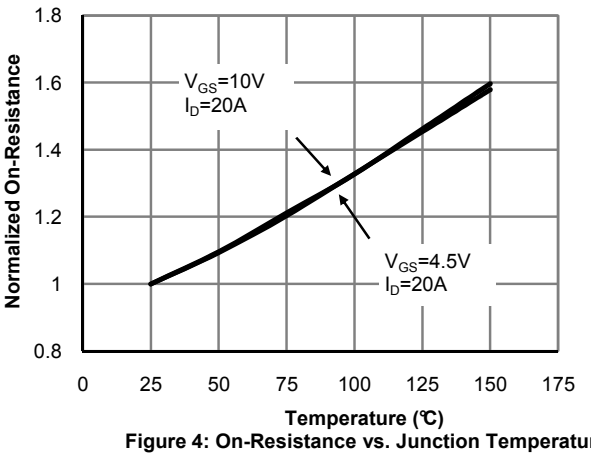

Figure 4: On-Resistance vs. Junction Temperature

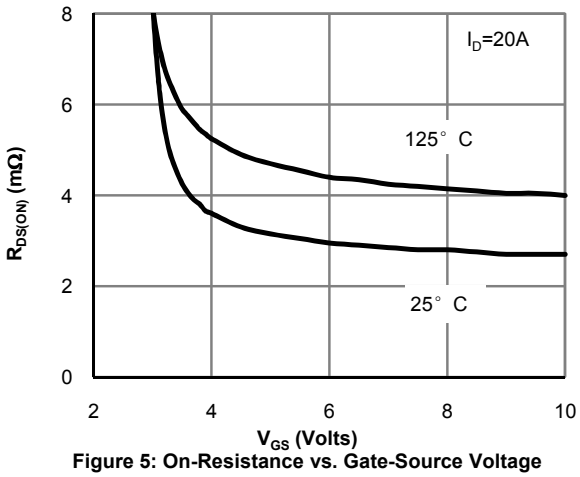

Figure 5: On-Resistance vs. Gate-Source Voltage

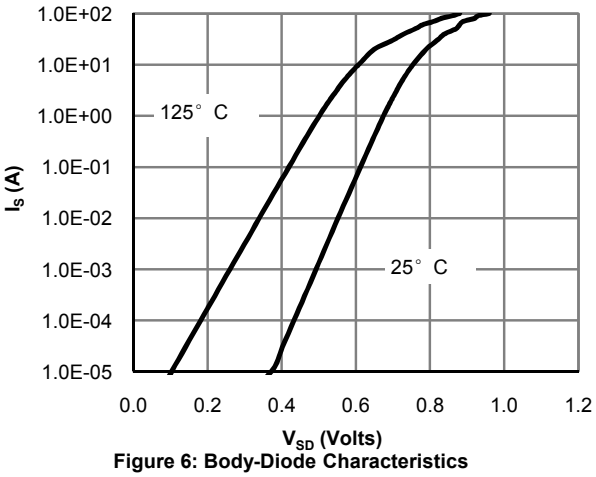

Figure 6: Body-Diode Characteristics

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■ Typical Characterisitics

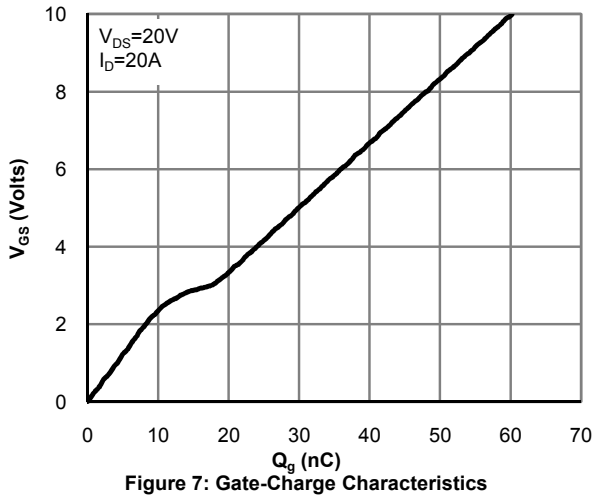

Figure 7: Gate-Charge Characteristics

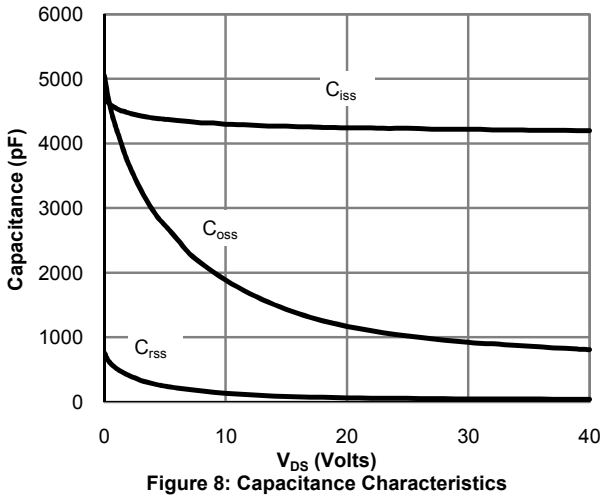

Figure 8: Capacitance Characteristics

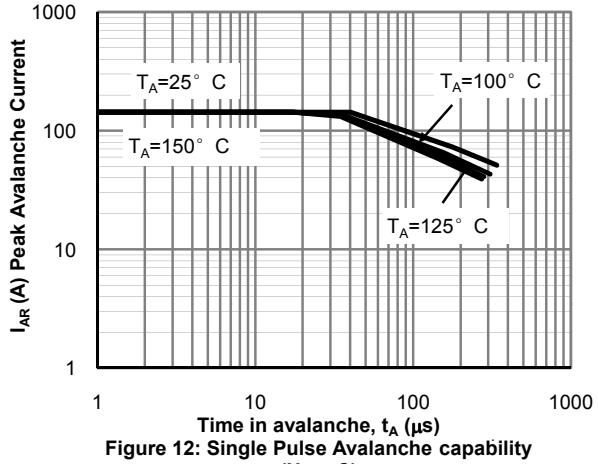

Figure 12: Single Pulse Avalanche capability (Note C)

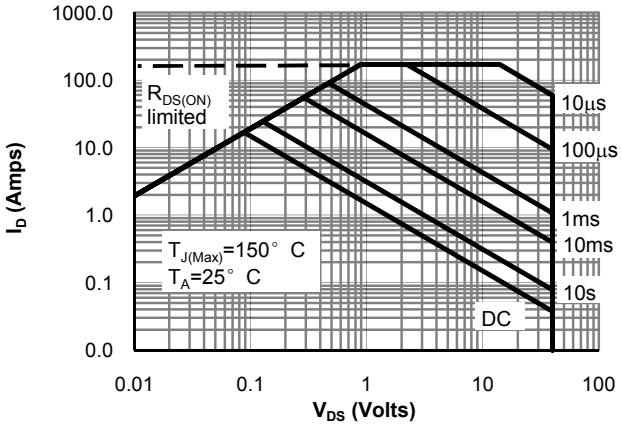

Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

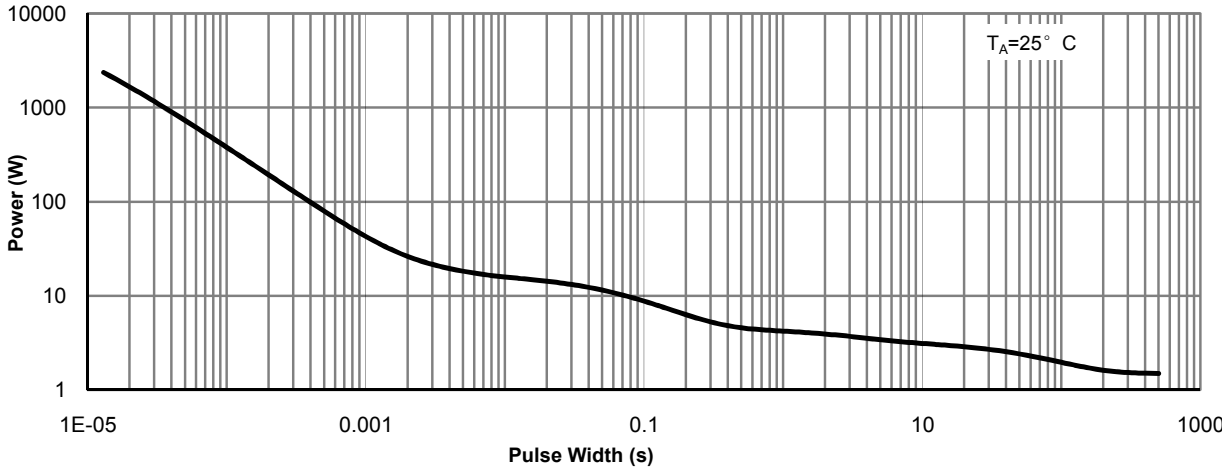

Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

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■ Typical Characterisitics

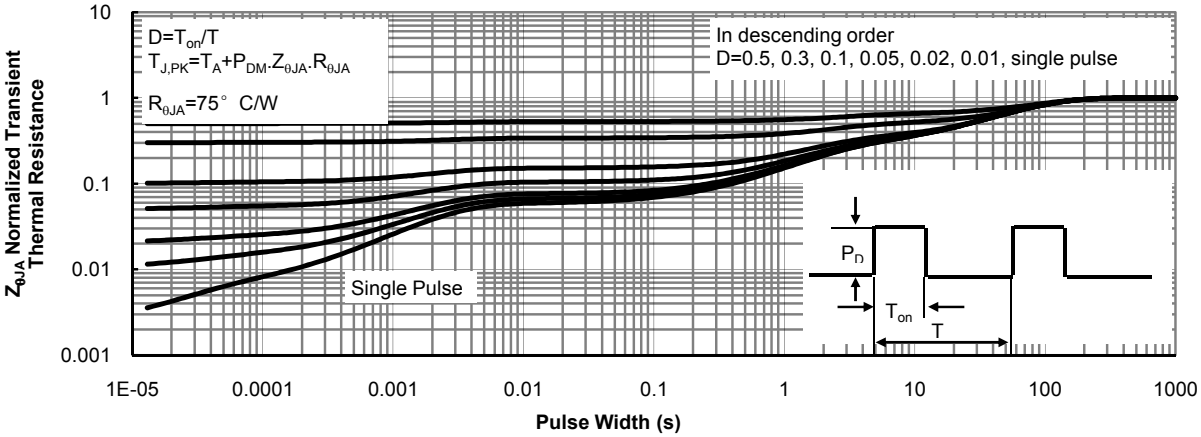

Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)